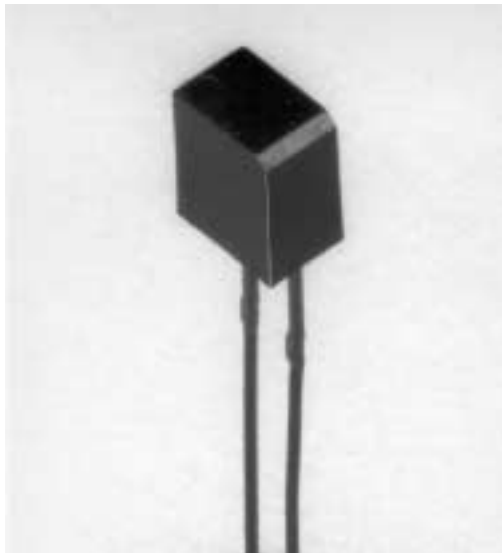
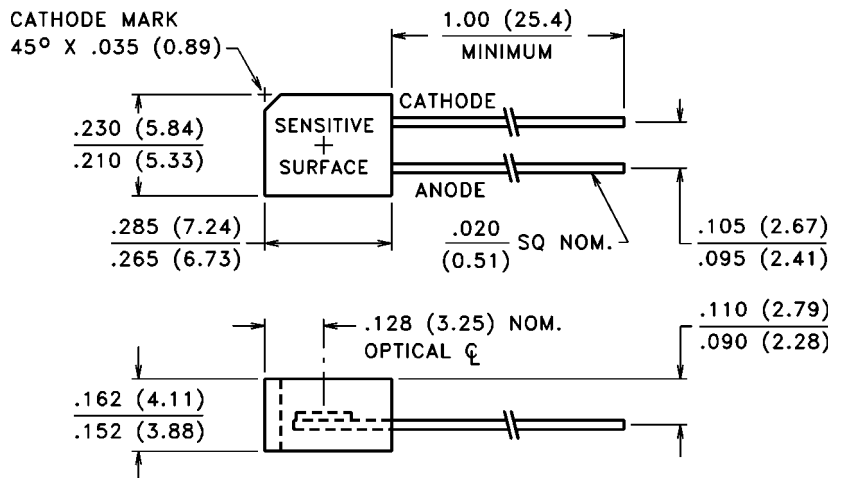




PACKAGE DIMENSIONS inch (mm)



PRODUCT DESCRIPTION

Planar silicon photodiode in a molded plastic sidelooker package. The package material is infrared transmitting (blocking visible light). These diodes exhibit low dark current and fast speed of response.

CASE 52 FLAT SIDELOOKER
CHIP ACTIVE AREA: .012 in² (7.45 mm²)

ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -40°C to 100°C
Operating Temperature: -40°C to 100°C

RoHS Compliant



ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTP curves, pages 45-46)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTP100H			UNITS
			Min.	Typ.	Max.	
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	35	55		μA
TC I _{SC}	I _{SC} Temperature Coefficient	2850 K		.24		%/°C
V _{OC}	Open Circuit Voltage	H = 100 fc, 2850 K		300		mV
TC V _{OC}	V _{OC} Temperature Coefficient	2850 K		-2.0		mV/°C
I _D	Dark Current	H = 0, V _R = 10 V			30	nA
R _{SH}	Shunt Resistance	H = 0, V = 10 mV		.25		GΩ
C _J	Junction Capacitance	H = 0, V = 3 V			50	pF
Re	Responsivity	940 nm	.036	.047		A/(W/cm ²)
S _R	Sensitivity	@ Peak		.50		A/W
λ _{range}	Spectral Application Range		725		1150	nm
λ _p	Spectral Response - Peak			925		nm
V _{BR}	Breakdown Voltage		30	140		V
θ _{1/2}	Angular Resp. - 50% Resp. Pt.			±70		Degrees
NEP	Noise Equivalent Power		2.5 x 10 ⁻¹⁴ (Typ.)			W/√Hz
D*	Specific Detectivity		1.1 x 10 ¹³ (Typ.)			cm√Hz/W